



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-20V	1.9Ω @ V _{GS} = -4.5V	-0.36A
	2.4Ω @ V _{GS} = -2.5V	-0.32A
	3.4Ω @ V _{GS} = -1.8V	-0.27A
	5.0Ω @ V _{GS} = -1.5V	-0.22A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power management functions
- Backlighting
- Load switches

Features and Benefits

- Low On-Resistance
- Low Input/Output Leakage
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

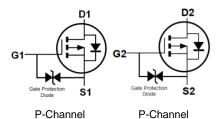
- Package: X2-DFN1010-6
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Weight: 0.0015 grams (Approximate)

X2-DFN1010-6 (Type UXC)

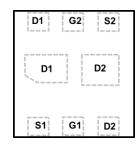




Bottom View



Equivalent Circuit



Pin-out Top View

Ordering Information (Note 4)

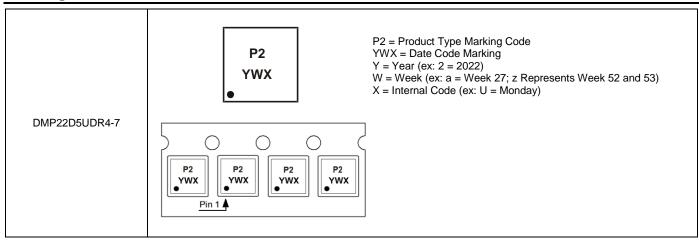
Part Number	Package	Tape Width (mm) Tape Pitch (mm) Packing			king
Part Number	Fackage	rape widin (ililii)	rape Fitch (IIIII)	Qty.	Carrier
DMP22D5UDR4-7	X2-DFN1010-6 (Type UXC)	8	4	5,000	Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	2	3	4	5	6	7	8	9	0	1	2	3
Week 1-26			27-52			53						
Code	A-Z			a-z z								
Internal Code	Sur	n	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		11		V	V	V	X		V		7

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	VDSS	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	ID	-0.36 -0.29	А
Maximum Continuous Body Diode Forward Current (Is	-0.3A	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-0.8	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.38	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	328	°C/W
Total Power Dissipation (Note 6)		PD	0.66	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	190	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:



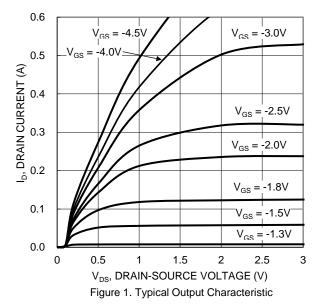
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		-20	-	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current @Tc = +25°C		_	_	-1	μΑ	V _{DS} = -16V, V _{GS} = 0V	
Gate-Source Leakage	Igss	1		±10	μΑ	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	-0.4	-	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
			1.6	1.9		$V_{GS} = -4.5V, I_{D} = -100mA$	
Static Drain-Source On-Resistance	Descour	1	2.2	2.4	Ω	$V_{GS} = -2.5V, I_D = -50mA$	
Static Dialii-Source Off-Resistance	RDS(ON)	1	3.2	3.4		$V_{GS} = -1.8V, I_{D} = -20mA$	
		1	4.1	5.0		$V_{GS} = -1.5V, I_{D} = -10mA$	
Diode Forward Voltage	VsD		-0.75	-1.1	V	$V_{GS} = 0V$, $I_{S} = -10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	17	_			
Output Capacitance	Coss		4.1	_	pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		2.7	_		1 = 1.0W112	
Total Gate Charge	Qg	1	0.3	_		15)/)/ 10)/	
Gate-Source Charge	Qgs	1	0.04	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V$ $I_{D} = -250 \text{mA}$	
Gate-Drain Charge	Q_{gd}	_	0.1	_		ID = -230IIIA	
Turn-On Delay Time	t _{D(ON)}	_	7.3	_			
Turn-On Rise Time	t _R	_	20.7	_	no	V _{DD} = -15V, V _{GS} = -4.5V	
Turn-Off Delay Time	tD(OFF)		185	_	ns	$R_G = 2\Omega$, $I_D = -200mA$	
Turn-Off Fall Time	t _F	_	97	_			

Notes:

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.





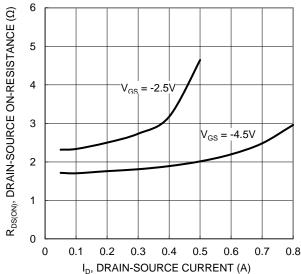


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

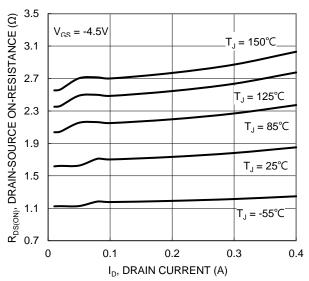
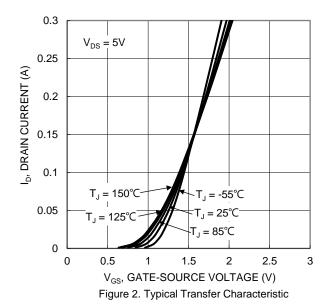


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



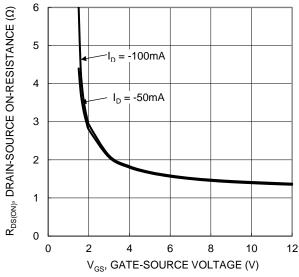
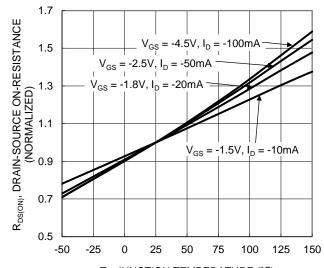


Figure 4. Typical Transfer Characteristic



 $\rm T_{J},\,JUNCTION\,TEMPERATURE$ (°C) Figure 6. On-Resistance Variation with Junction Temperature



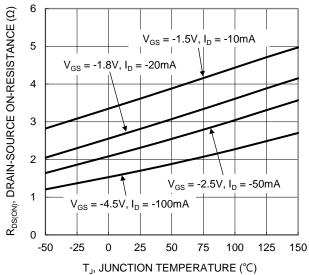
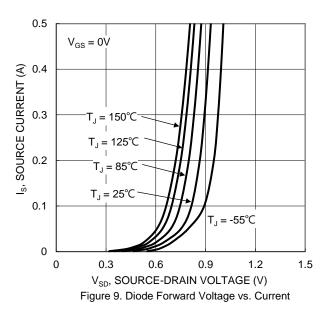
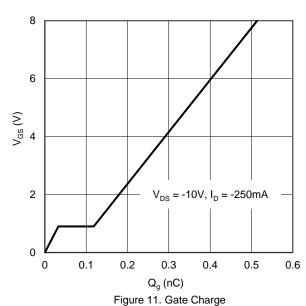


Figure 7. On-Resistance Variation with Junction Temperature





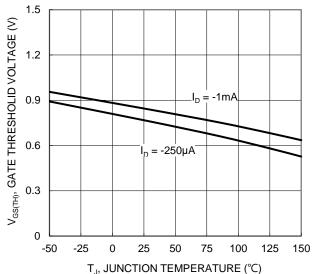
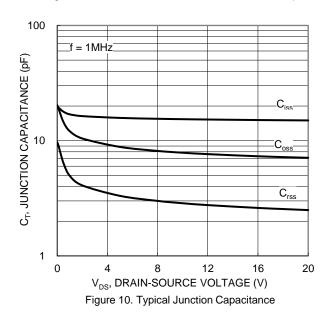


Figure 8. Gate Threshold Variation vs. Junction Temperature



1 R_{DS(ON)} ID, DRAIN CURRENT (A) 0.1 = 150°C Pw = 100ms $T_A = 25^{\circ}C$ Single Pulse Pw = 1sDUT on 1*MRF Pw = 10sBoard DC $V_{GS} = -4.5V$ 0.01 0.1 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



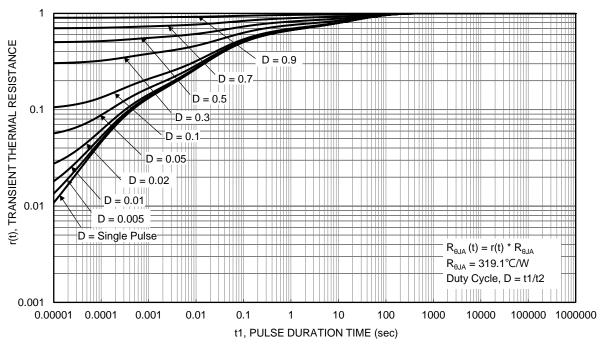


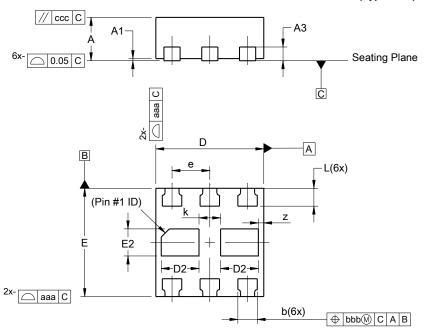
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1010-6 (Type UXC)

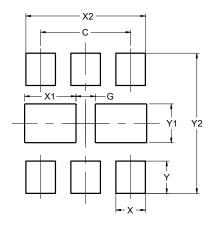


X2-DFN1010-6							
(Type UXC)							
Dim	Min	Min Max Ty					
Α	-	0.40	0.39				
A1	-	0.05					
A3	-		0.127				
b	0.13	0.23	0.18				
D	0.95	1.05	1.00				
D2	0.30	0.40	0.35				
Е	0.95	1.05	1.00				
E2	0.20	0.30					
е	0.	350 BS	С				
L	0.115	0.215	0.165				
k	-		0.20				
Z	0.02 0.08 0.05						
aaa	0.08						
bbb	0.07						
CCC	0.05						
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1010-6 (Type UXC)



Dimensions	Value
Dilliensions	(in mm)
C	0.700
G	0.300
Х	0.230
X1	0.450
X2	0.930
Υ	0.250
Y1	0.300
Y2	1.085



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